Application No.: 10/560,831 Docket No.: 053385

AMENDMENTS TO THE CLAIMS

This listing of claims replaces all prior versions of claims in the application.

1-3 (Cancelled).

4. (Currently Amended): A method for producing a rare earth-iron-boron based magnet, the method comprising:

supporting a Nd-Fe-B based sintered body sintered original magnet in a reduced pressure vessel containing several tens ppm or less of oxygen and water vapor, the Nd-Fe-B based sintered original magnet having grain boundary layer comprising Nd rich phase surrounding a main crystal of particle diameter of 6-10 μm comprising Nd₂Fe₁₄B, the Nd-Fe-B based sintered body original magnet having a shape of plate or of hollow cylinder with a thickness of 10 mm or less;

physically depositing supplying a vapor or fine particles of element M (element M is at least one rare earth element selected from Pr, Dy, Tb, and Ho) or an alloy containing the element M onto the entire surface or a portion of the surface of the Nd-Fe-B based sintered body to form a film of the element M; and then original magnet; and

heating the <u>original</u> magnet at 500-1000°C so as to diffuse and penetrate the element M into the <u>original</u> magnet from the surface thereof so as to form a crystal grain boundary layer enriched in the element M by reaction with the Nd rich phase disposed between main crystals,

wherein the <u>rare earth-iron-boron based</u> magnet satisfies following (A) and (D): (A) to (C):

(A) $\text{Hcj} \ge 1 + 0.2 \text{ x M}$ and $0.05 \le M \le 10$, where Hcj is coercive force in MA/m, and M is concentration of the element M in mass % in a whole magnet,

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(B) Br \geq 1.68 – 0.17 x Hcj, where Br is the residual magnetic flux density (unit: T), and

(C) the element M reacting reacted with the Nd rich phase distributes in a range of 10-1000µm from exposed surfaces, and (D) wherein concentration of the element M increases as the erystal grain boundary layer approaches to surface of the magnet, and the concentration of element M is 50 mass % or more at 10 µm from the surface.

5. (Cancelled).

6. (Currently Amended): A method for producing a rare earth-iron-boron based magnet according to claim 4, the method comprising:

supporting a Nd-Fe-B based sintered body sintered original magnet in a reduced pressure vessel containing several tens ppm or less of oxygen and water vapor, the Nd-Fe-B based sintered body original magnet having grain boundary layer comprising Nd rich phase surrounding a main crystal of particle diameter of 6–10 μm comprising Nd₂Fe₁₄B, the Nd-Fe-B based sintered body original magnet having a shape of plate or of hollow cylinder with a thickness of 10 mm or less; and

depositing supplying, by sputtering, fine particles of element M (element M is at least one rare earth element selected from Pr, Dy, Tb, and Ho) or an alloy containing the element M onto the entire surface or a portion of the surface of the Nd-Fe-B based sintered body to form a film of the element M,

wherein the magnet is heated at 500-1000°C in the depositing supplying step so as to diffuse and penetrate the element M into the magnet from the surface thereof so as to form a crystal grain

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boundary layer enriched in the element M by reaction with the Nd rich phase, the magnet having the rare earth-rich grain boundary layer disposed between main crystals,

wherein the <u>rare earth-iron-boron based</u> magnet satisfies following (A) and (D): (A) to (C):

(A) $\text{Hcj} \ge 1+0.2 \text{ x M}$ and $0.05 \le M \le 10$, where Hcj is coercive force in MA/m, and M is concentration of the element M in mass % in a whole magnet,

(B) Br \geq 1.68 – 0.17 x Hcj, where Br is the residual magnetic flux density (unit: T), and

(C) the element M reacting reacted with the Nd rich phase distributes in a range of 10-1000µm from exposed surfaces, and (D) wherein concentration of the element M increases as the crystal grain boundary layer approaches to surface of the magnet, and the concentration of element M is 50 mass % or more at 10 µm from the surface.